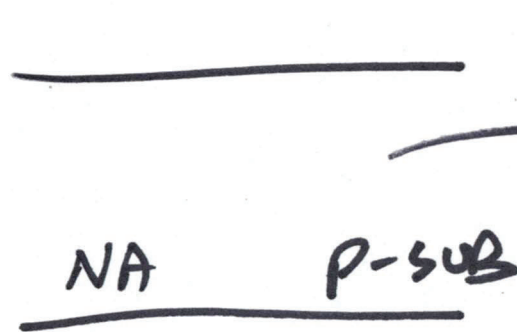


EE 421 / ECG 621

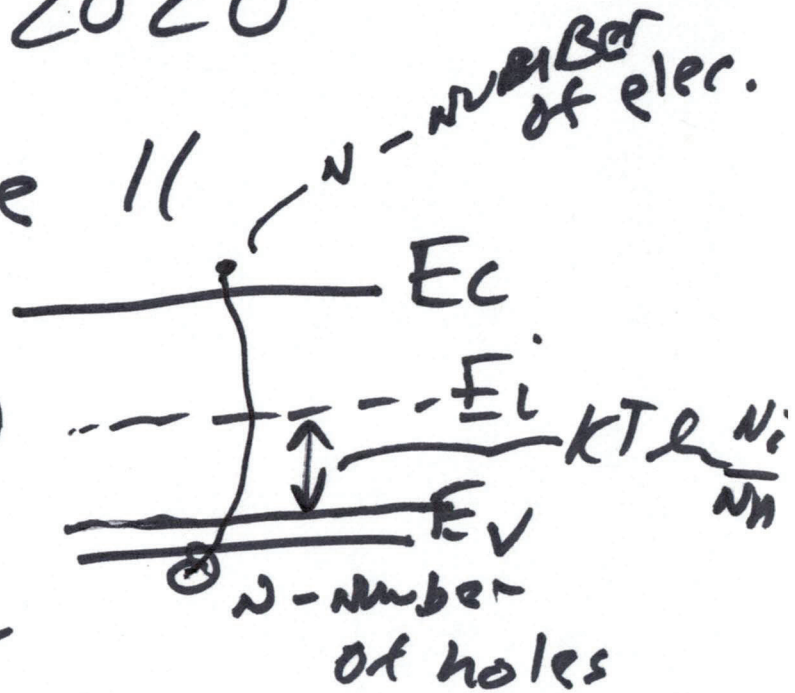
Digital IC Design

Sept. 30, 2020

Lecture 11



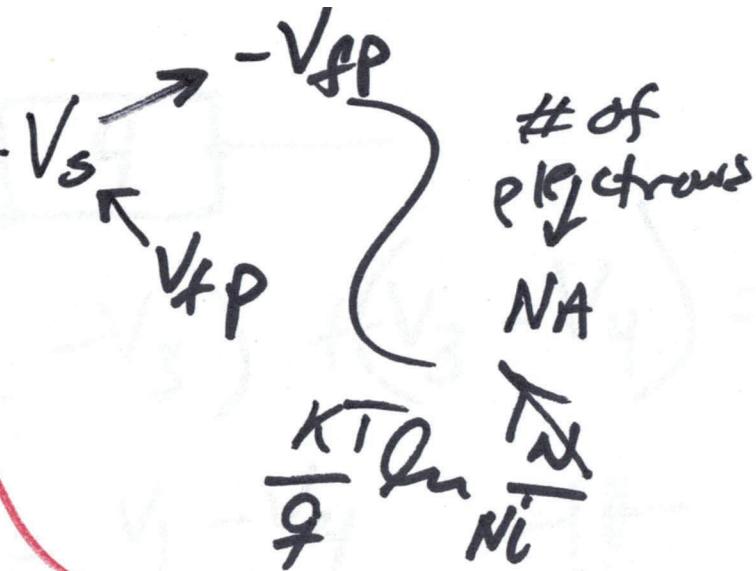
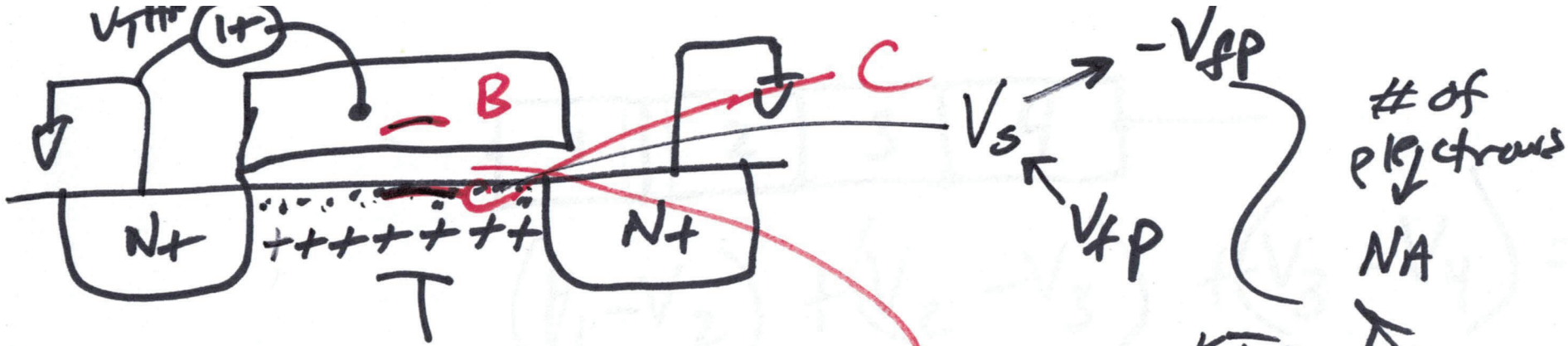
$P = \# \text{ of holes}$
 $NA + n_i = NA$



$NA = \# \text{ of acceptor atoms in substrate}$

Boron - 3 valence electrons

1)



P-sub

$$V_{FP} = \frac{KT}{q} \ln \frac{N_i}{N_A}$$

$$C_{ox} = \frac{\epsilon_{ox}}{t_{ox}}$$

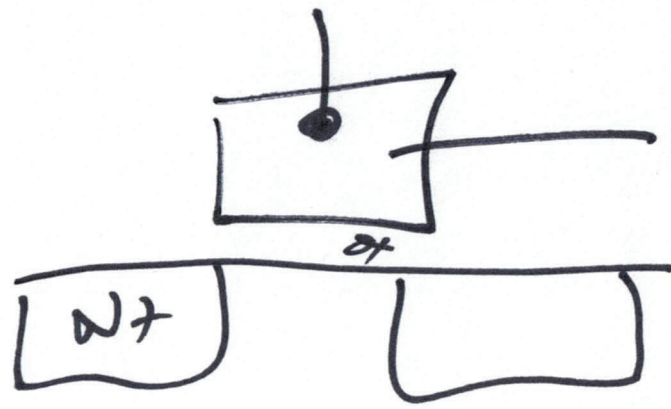
$$Q'_{b0} = \sqrt{2qNA \cdot | -2V_{FP} |}$$

$$V_{BC} = \frac{Q'_b}{C_{ox}}$$

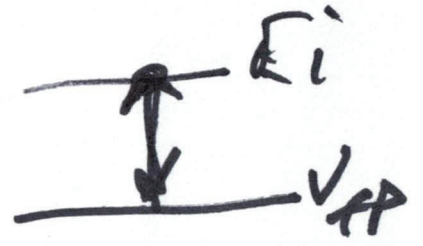
$$V_B = \frac{Q'_b}{C_{ox}} - V_S \Rightarrow$$

$$\frac{Q'_b}{C_{ox}} - 2V_{FP}$$

2)

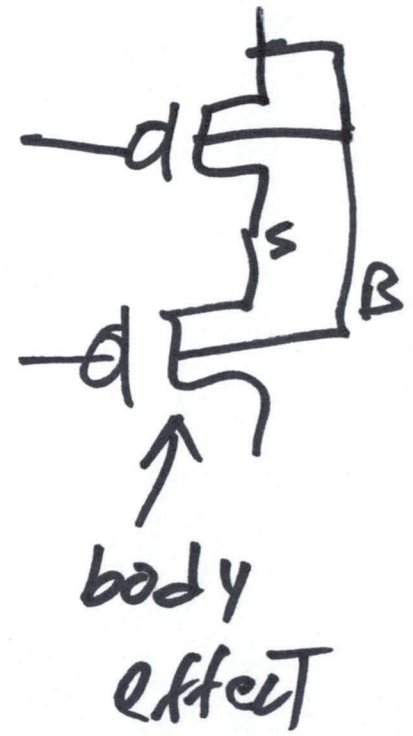
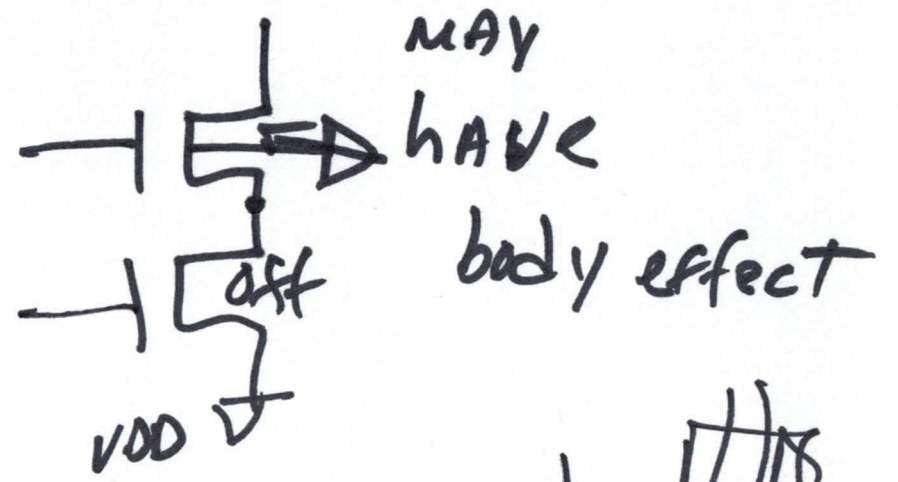
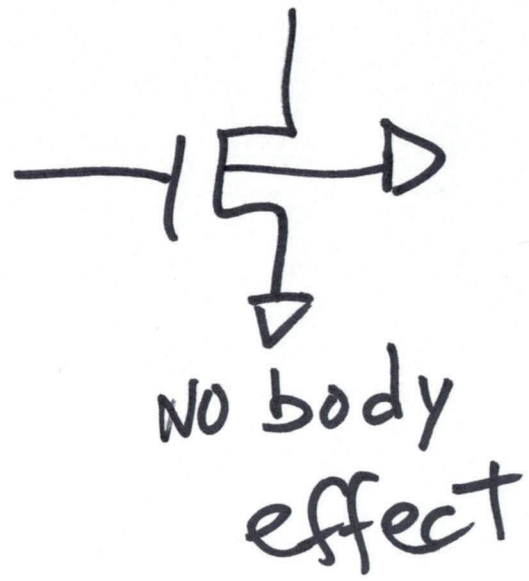


$$N_{D, poly} = \frac{kT}{q} \ln \frac{N_{D, poly}}{N_i}$$



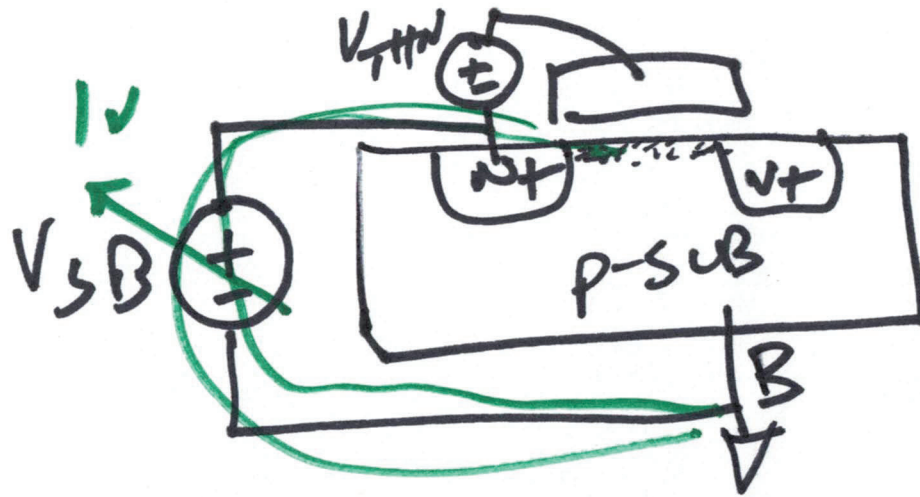
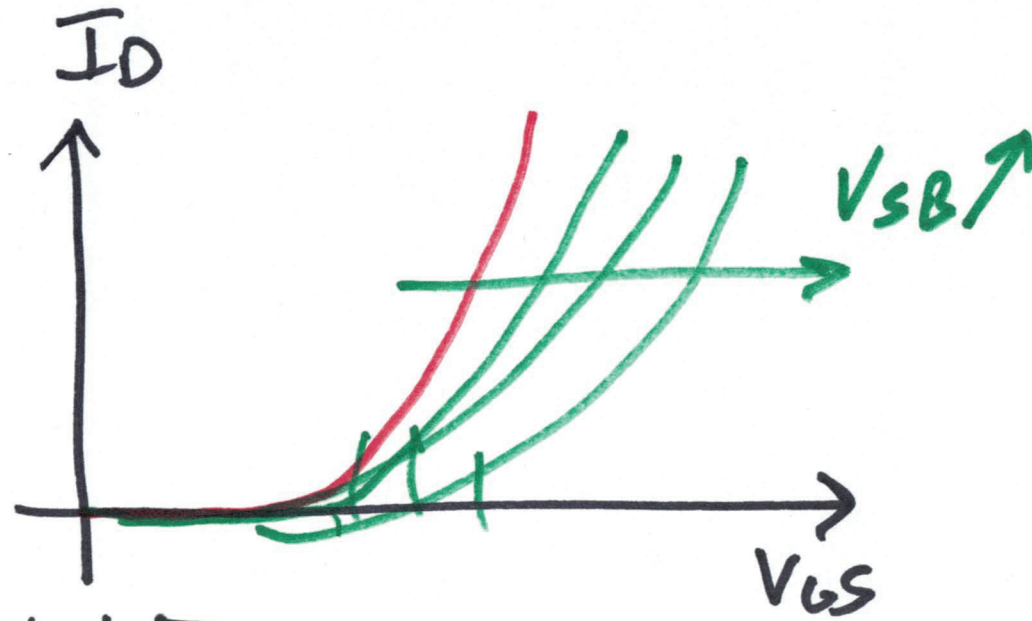
$$V_{ms} = \frac{kT}{q} \ln \frac{N_{D, poly}}{N_i} - \frac{kT}{q} \ln \frac{N_i}{N_A}$$

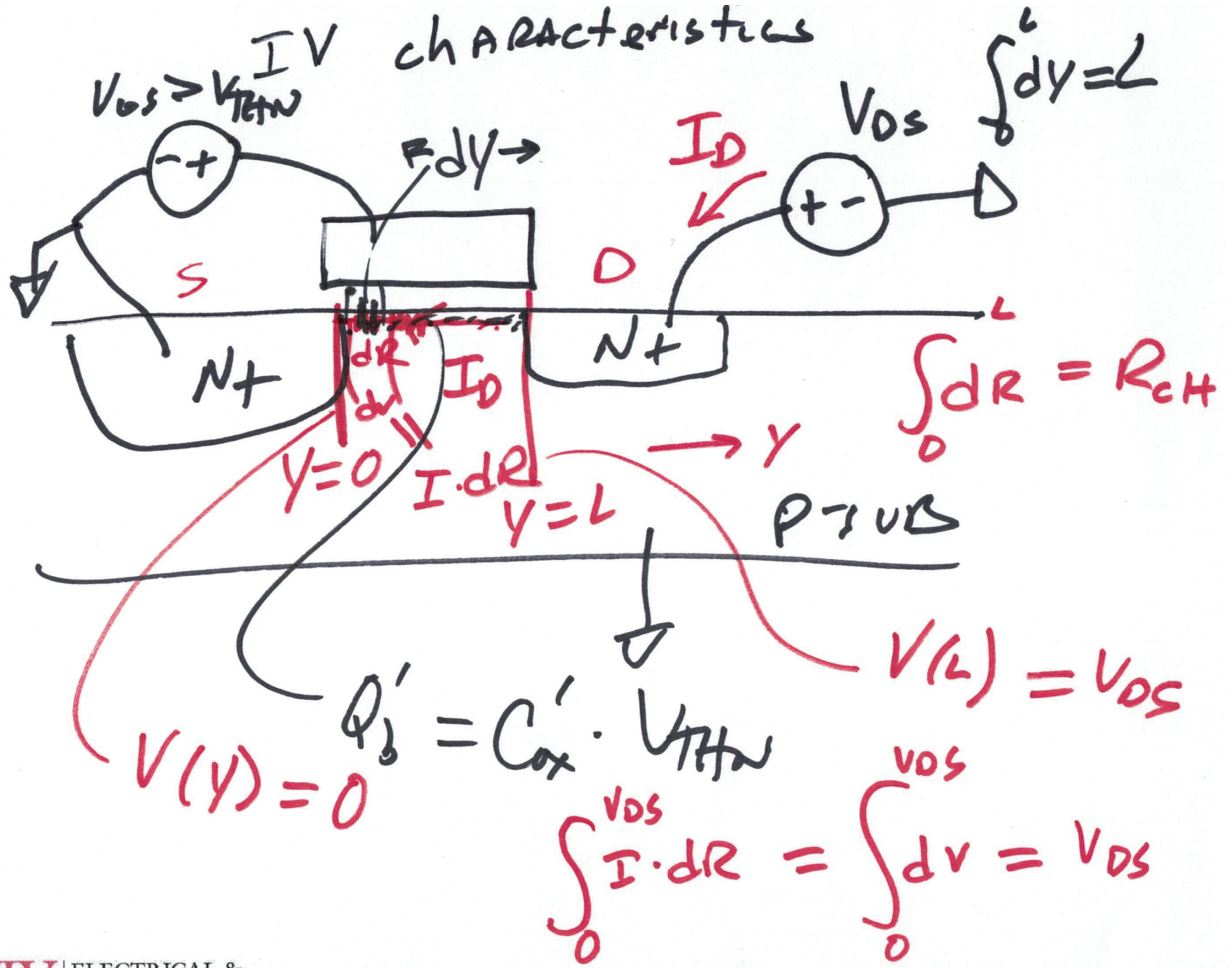
5)

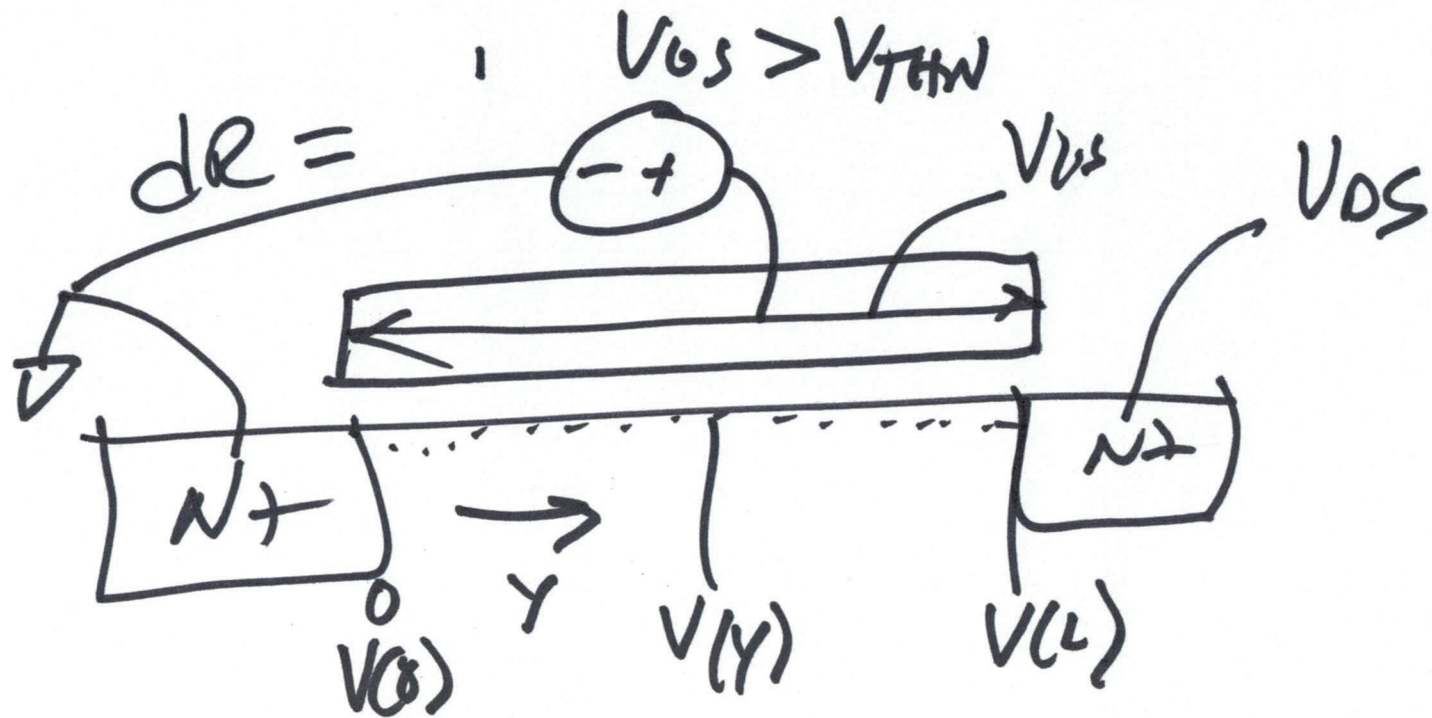


6)

Body effect







$$Q'_b = C_{ox} \cdot V_{THN}$$

$$Q'_{ch} = C_{ox} (V_{GS} - V(y))$$

$$Q'_I = Q'_{ch} - Q'_b = C_{ox} (V_{GS} - V(L) - V_{THN})$$

$$dR = \frac{dy}{w} \cdot \frac{1}{Q_i(y) \cdot \mu_n}$$

μ_n ← mobility = $\frac{\text{speed}}{\text{Electric field}}$
 $(\frac{\text{cm}^2}{\text{V}\cdot\text{s}})$

$$dV(y) = I_D \cdot dR = \frac{I_D}{w \cdot \mu_n \cdot Q_i'(y)} \cdot dy$$

$$\int_0^L I_D \cdot dy = \int_0^{V_{DS}} (w \mu_n \cdot C_{ox} (V_{GS} - V(y) - V_{THN})) \cdot dV(y)$$

$$I_D \cdot L =$$

$$K_{PN} = \mu_n \cdot C_{ox}$$

$$K_{PP} = \mu_p \cdot C_{ox}$$

$$I_0 \cdot L = \int_0^{V_{DS}} W \mu_n C_{ox} (V_{GS} - V_{GS}(y) - V_{THN}) dV(y)$$

$$= W \mu_n C_{ox} \left[\int_0^{V_{DS}} V_{GS} \cdot dV(y) - \int_0^{V_{DS}} V(y) dV(y) - \int_0^{V_{DS}} V_{THN} dV(y) \right]$$

$\int_0^{V_{DS}} V_{GS} \cdot dV(y) \rightarrow V_{GS} \cdot V_{DS}$
 $\int_0^{V_{DS}} V(y) dV(y) \rightarrow \frac{1}{2} V_{DS}^2$
 $\int_0^{V_{DS}} V_{THN} dV(y) \rightarrow V_{DS} \cdot V_{THN}$

11)

$$I_{D,L} = \frac{W}{L} \mu_n C_{ox} \left(V_{GS} V_{DS} - \frac{1}{2} V_{DS}^2 - V_{GS} V_{THN} \right)$$

$$I_D = \frac{W}{L} \mu_n C_{ox} \left((V_{GS} - V_{THN}) V_{DS} - \frac{1}{2} V_{DS}^2 \right)$$

triode

$$V_{GS} > V_{THN}$$

$$V_{DS} \leq V_{GS} - V_{THN}$$

$$V_{DS} = V_{GS} - V_{THN}$$

$$I_D = \frac{W}{L} \frac{\mu_n C_{ox}}{2} \underbrace{(V_{GS} - V_{THN})^2}_{= V_{DS}}$$

saturated

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